

# 100V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
100V	$17.4 \text{m}\Omega @ V_{GS} = 10 \text{V}$	59A
	$30.3 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	45A

## **Description and Applications**

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

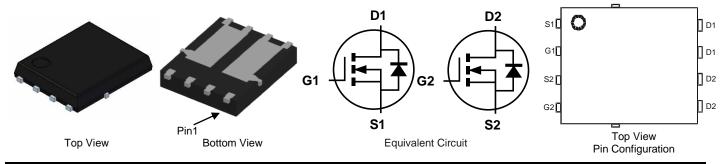
- Synchronous Rectifier
- DC-DC Converters
- Primary Side Switching

### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH10H017LPDQ</u>)

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



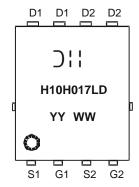
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H017LPD-13	PowerDI5060-8 (Type E)	2500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



⊃¦¦= Manufacturer's Marking H10H017LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

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## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		I <sub>D</sub>	59 42	А
Maximum Body Diode Forward Current (Note 6)	Is	60	Α	
Pulsed Drain Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Limited)	I <sub>DM</sub>	236	Α	
Pulsed Body Diode Forward Current (10µs Pulse, T <sub>C</sub> = +25°C, Package Li	I <sub>SM</sub>	236	Α	
Avalanche Current, L = 3mH (Note 9)	I <sub>AS</sub>	10	Α	
Avalanche Energy, L = 3mH (Note 9)	E <sub>AS</sub>	150	mJ	
Avalanche Current, L = 1mH (Note 9)	I <sub>AS</sub>	10	Α	
Avalanche Energy, L = 1mH (Note 9)	E <sub>AS</sub>	50	mJ	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	56	°C/W
Total Power Dissipation	T <sub>C</sub> = +25°C	P <sub>D</sub>	93	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0JC</sub>	1.6	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

## **Electrical Characteristics** (@ $T_C = \pm 25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	0	_	13.7	17.4	mΩ	$V_{GS} = 10V, I_D = 17A$	
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	_	23.8	30.3	11122	$V_{GS} = 4.5V, I_D = 10A$	
Diode Forward Voltage	V <sub>SD</sub>	_	_	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 17A	
DYNAMIC CHARACTERISTICS (Note 8)				•	•		
Input Capacitance	C <sub>iss</sub>	_	1986	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	333	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	20	_			
Gate Resistance	R <sub>G</sub>	_	1.17	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	14.4	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	28.6	_	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 20A	
Gate-Source Charge	Q <sub>gs</sub>	_	5.2	_	110	$V_{DS} = 50V$ , $I_D = 20A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	8.2	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.8	_		V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V,	
Turn-On Rise Time	t <sub>R</sub>	_	16.3	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		32.6	_	ns	$R_G = 11\Omega$ , $I_D = 20A$	
Turn-Off Fall Time	t <sub>F</sub>		21.6	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	40.6	_	ns	I <sub>F</sub> = 17A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	dy Diode Reverse Recovery Charge $Q_{RR}$ — 58.1 — nC $I_F$ = 17A, di/dt = 10		I <sub>F</sub> = 17A, di/dt = 100A/µs				

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
   Thermal resistance from junction to solder point (on the exposed drain pin).
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

- 9.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.





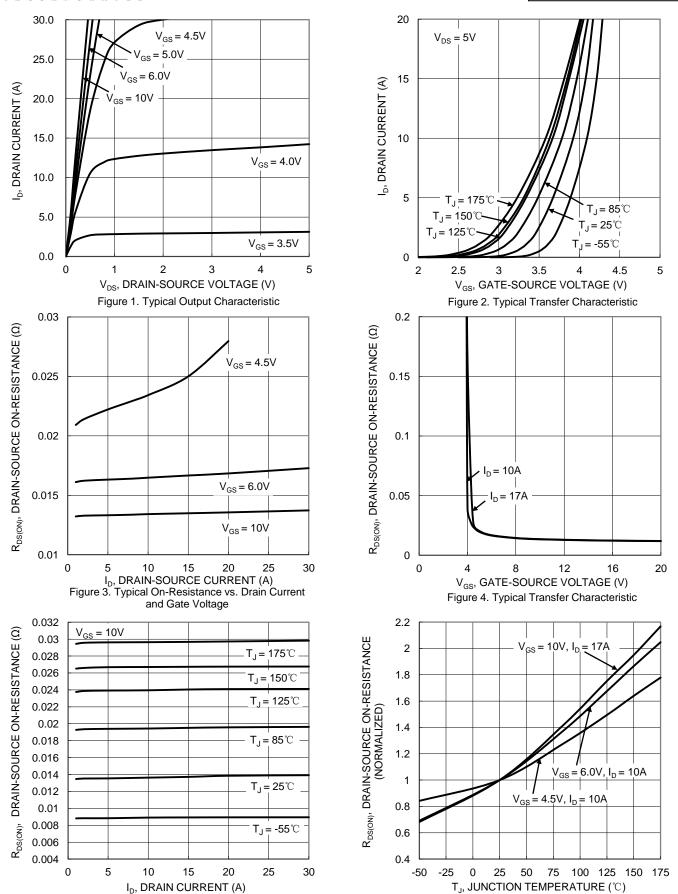


Figure 5. Typical On-Resistance vs. Drain Current

and Temperature

Figure 6. On-Resistance Variation with Temperature





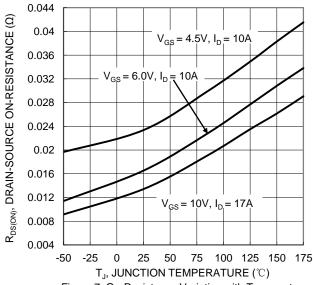


Figure 7. On-Resistance Variation with Temperature

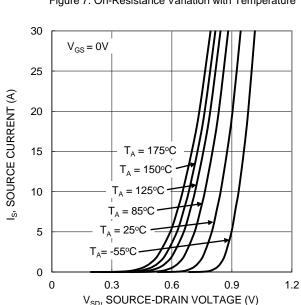


Figure 9. Diode Forward Voltage vs. Current

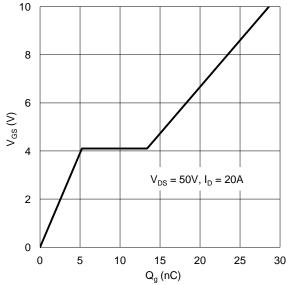


Figure 11. Gate Charge

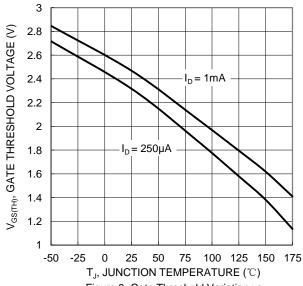


Figure 8. Gate Threshold Variation vs. JunctionTemperature

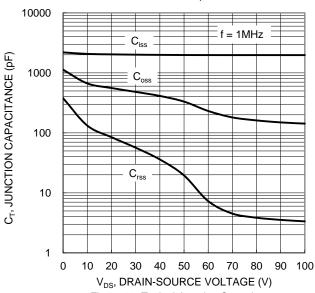


Figure 10. Typical Junction Capacitance

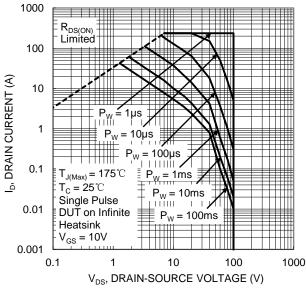


Figure 12. SOA, Safe Operation Area



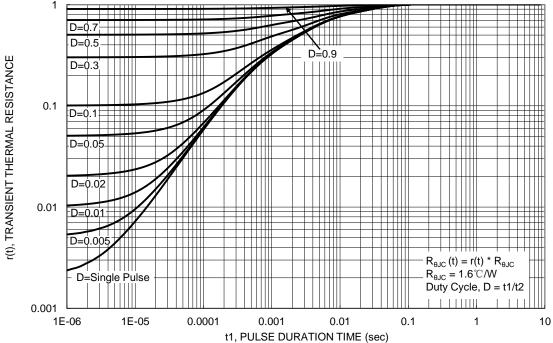


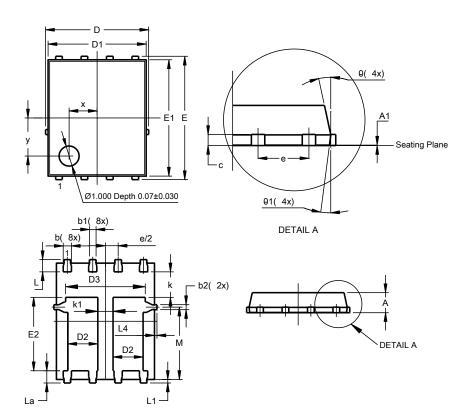
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type E)

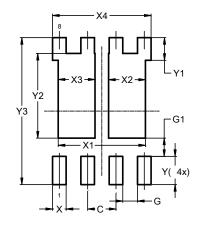


PowerDI5060-8						
(Type E)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
С	0.23	0.33	0.277			
D	5	.15 BS0				
D1	4.85	4.95	4.90			
D2	1.40	1.60	1.50			
D3	-	-	3.98			
Е	6	.15 BS0	5			
E1	5.75	5.85	5.80			
E2	3.56	3.76	3.66			
е	1	.27BSC				
k	-	-	1.27			
k1	0.56	-	-			
L	0.51	0.71	0.61			
La	0.51	0.71	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
М	3.50	3.71	3.605			
X	-	-	1.400			
У	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type E)



Dimensions	Value		
	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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